

Silicon NPN Power Transistors

2SD884

DESCRIPTION

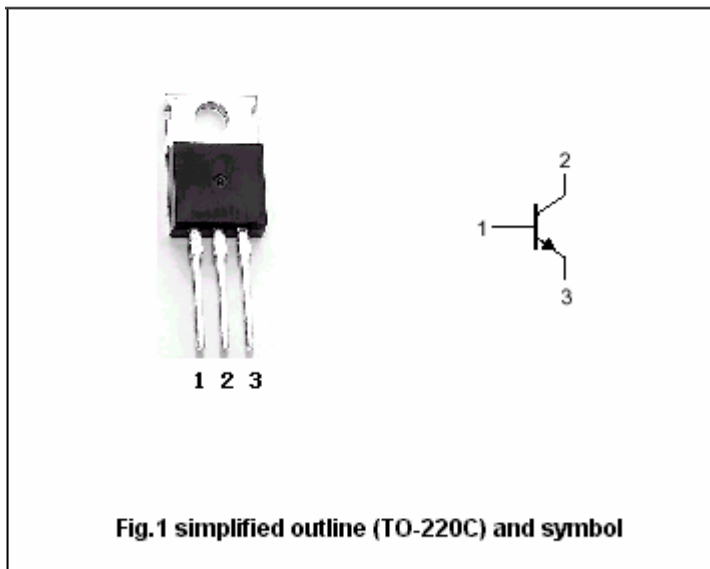
- With TO-220C package
- High voltage;high speed
- Large P_C

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	330	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		7	A
I_{CP}	Collector current-Peak		10	A
I_{CP}	Collector current-Peak	nonrepetitive	15	A
P_T	Total power dissipation	$T_C=25^\circ C$	40	W
T_j	Junction temperature		150	$^\circ C$
T_{stg}	Storage temperature		-55~150	$^\circ C$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	200			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A			1.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =5A ; I _B =0.5A			1.2	V
I _{CES}	Collector cut-off current	V _{CE} =330V; V _{EB} =0			0.1	mA
		V _{CE} =300V; V _{EB} =0, T _a =100 °C			1.0	
I _{EBO}	Emitter cut-off current	V _{EB} =6.0V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =4V	10		45	
t _f	Fall time	I _C =5A ; -V _{EB} =5V I _{B1} =0.8A; R _B =0.5Ω			0.75	μs

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PACKAGE OUTLINE

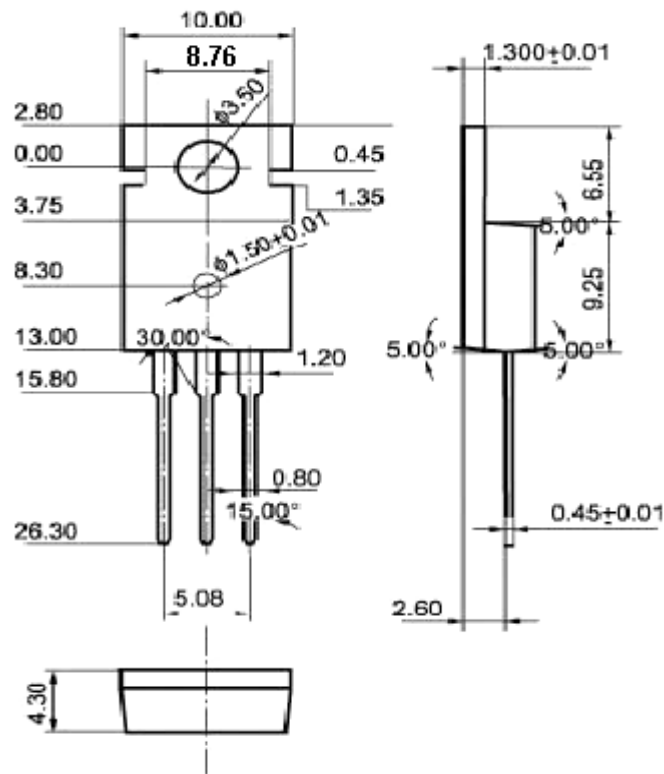


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)